



# FQPF7N60

## 600V N-Channel MOSFET

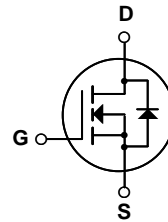
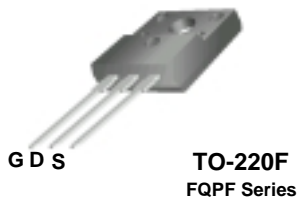
### General Description

These N-Channel enhancement mode power field effect transistors are produced using Corise Semiconductor's proprietary, planar stripe, DMOS technology.

This advanced technology has been especially tailored to minimize on-state resistance, provide superior switching performance, and withstand high energy pulse in the avalanche and commutation mode. These devices are well suited for high efficiency switch mode power supply.

### Features

- 4.3A, 600V,  $R_{DS(on)} = 1.0\Omega @ V_{GS} = 10V$
- Low gate charge ( typical 29 nC)
- Low Crss ( typical 16 pF)
- Fast switching
- 100% avalanche tested
- Improved dv/dt capability



### Absolute Maximum Ratings T<sub>C</sub> = 25°C unless otherwise noted

Symbol	Parameter	FQPF7N60	Units
V <sub>DSS</sub>	Drain-Source Voltage	600	V
I <sub>D</sub>	Drain Current - Continuous (T <sub>C</sub> = 25°C) - Continuous (T <sub>C</sub> = 100°C)	4.3	A
		2.7	A
I <sub>DM</sub>	Drain Current - Pulsed (Note 1)	17.2	A
V <sub>GSS</sub>	Gate-Source Voltage	± 30	V
E <sub>AS</sub>	Single Pulsed Avalanche Energy (Note 2)	580	mJ
I <sub>AR</sub>	Avalanche Current (Note 1)	4.3	A
E <sub>AR</sub>	Repetitive Avalanche Energy (Note 1)	4.8	mJ
dv/dt	Peak Diode Recovery dv/dt (Note 3)	4.5	V/ns
P <sub>D</sub>	Power Dissipation (T <sub>C</sub> = 25°C) - Derate above 25°C	48	W
		0.38	W/°C
T <sub>J</sub> , T <sub>STG</sub>	Operating and Storage Temperature Range	-55 to +150	°C
T <sub>L</sub>	Maximum lead temperature for soldering purposes, 1/8" from case for 5 seconds	300	°C

### Thermal Characteristics

Symbol	Parameter	Typ	Max	Units
R <sub>θJC</sub>	Thermal Resistance, Junction-to-Case	--	2.60	°C/W
R <sub>θJA</sub>	Thermal Resistance, Junction-to-Ambient	--	62.5	°C/W

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
<b>Off Characteristics</b>						
$BV_{DSS}$	Drain-Source Breakdown Voltage	$V_{GS} = 0\text{ V}, I_D = 250\ \mu\text{A}$	600	--	--	V
$\frac{\Delta BV_{DSS}}{\Delta T_J}$	Breakdown Voltage Temperature Coefficient	$I_D = 250\ \mu\text{A}$ , Referenced to 25°C	--	0.67	--	V/°C
$I_{DSS}$	Zero Gate Voltage Drain Current	$V_{DS} = 600\text{ V}, V_{GS} = 0\text{ V}$	--	--	10	$\mu\text{A}$
		$V_{DS} = 480\text{ V}, T_C = 125^\circ\text{C}$	--	--	100	$\mu\text{A}$
$I_{GSSF}$	Gate-Body Leakage Current, Forward	$V_{GS} = 30\text{ V}, V_{DS} = 0\text{ V}$	--	--	100	nA
$I_{GSSR}$	Gate-Body Leakage Current, Reverse	$V_{GS} = -30\text{ V}, V_{DS} = 0\text{ V}$	--	--	-100	nA

<b>On Characteristics</b>						
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = 250\ \mu\text{A}$	3.0	--	5.0	V
$R_{DS(on)}$	Static Drain-Source On-Resistance	$V_{GS} = 10\text{ V}, I_D = 2.2\text{ A}$	--	0.8	1.0	$\Omega$
$g_{FS}$	Forward Transconductance	$V_{DS} = 50\text{ V}, I_D = 2.2\text{ A}$ (Note 4)	--	6.4	--	S

<b>Dynamic Characteristics</b>						
$C_{iss}$	Input Capacitance	$V_{DS} = 25\text{ V}, V_{GS} = 0\text{ V},$ $f = 1.0\text{ MHz}$	--	1100	1430	pF
$C_{oss}$	Output Capacitance		--	135	175	pF
$C_{rss}$	Reverse Transfer Capacitance		--	16	21	pF

<b>Switching Characteristics</b>							
$t_{d(on)}$	Turn-On Delay Time	$V_{DD} = 300\text{ V}, I_D = 7.4\text{ A},$ $R_G = 25\ \Omega$	--	30	70	ns	
$t_r$	Turn-On Rise Time		--	80	170	ns	
$t_{d(off)}$	Turn-Off Delay Time		(Note 4, 5)	--	65	140	ns
$t_f$	Turn-Off Fall Time		(Note 4, 5)	--	60	130	ns
$Q_g$	Total Gate Charge	$V_{DS} = 480\text{ V}, I_D = 7.4\text{ A},$ $V_{GS} = 10\text{ V}$	--	29	38	nC	
$Q_{gs}$	Gate-Source Charge		(Note 4, 5)	--	7	--	nC
$Q_{gd}$	Gate-Drain Charge		(Note 4, 5)	--	14.5	--	nC

<b>Drain-Source Diode Characteristics and Maximum Ratings</b>						
$I_S$	Maximum Continuous Drain-Source Diode Forward Current	--	--	4.3	A	
$I_{SM}$	Maximum Pulsed Drain-Source Diode Forward Current	--	--	17.2	A	
$V_{SD}$	Drain-Source Diode Forward Voltage	$V_{GS} = 0\text{ V}, I_S = 4.3\text{ A}$	--	--	1.4	V
$t_{rr}$	Reverse Recovery Time	$V_{GS} = 0\text{ V}, I_S = 7.4\text{ A},$ $di_F / dt = 100\text{ A}/\mu\text{s}$ (Note 4)	--	320	--	ns
$Q_{rr}$	Reverse Recovery Charge		--	2.4	--	$\mu\text{C}$

**Notes:**

1. Repetitive Rating : Pulse width limited by maximum junction temperature
2.  $L = 57.6\text{ mH}, I_{AS} = 4.3\text{ A}, V_{DD} = 50\text{ V}, R_G = 25\ \Omega$ , Starting  $T_J = 25^\circ\text{C}$
3.  $I_{SD} \leq 7.4\text{ A}, di/dt \leq 200\text{ A}/\mu\text{s}, V_{DD} \leq BV_{DSS}$ , Starting  $T_J = 25^\circ\text{C}$
4. Pulse Test : Pulse width  $\leq 300\ \mu\text{s}$ , Duty cycle  $\leq 2\%$
5. Essentially independent of operating temperature

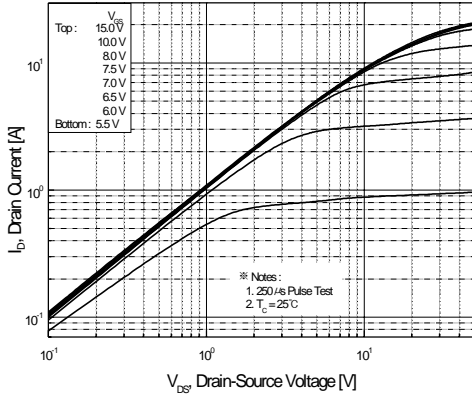


Figure 1. On-Region Characteristics

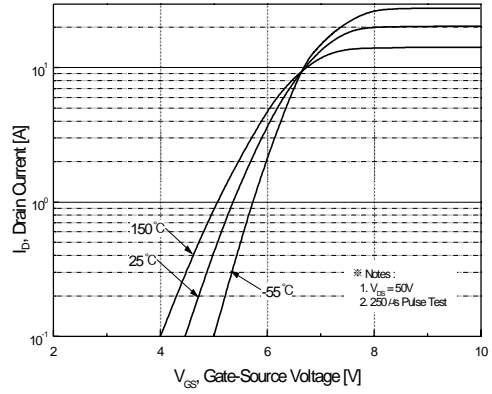


Figure 2. Transfer Characteristics

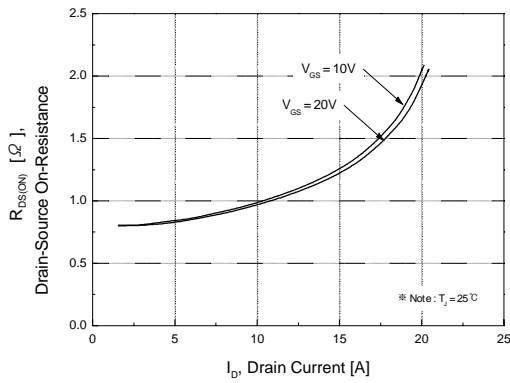


Figure 3. On-Resistance Variation vs. Drain Current and Gate Voltage

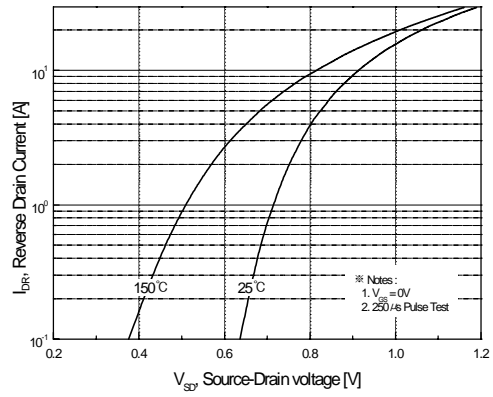


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature

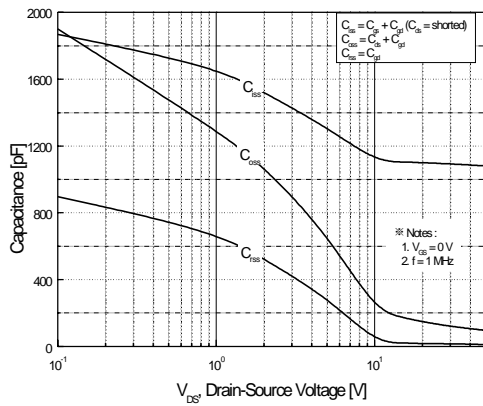


Figure 5. Capacitance Characteristics

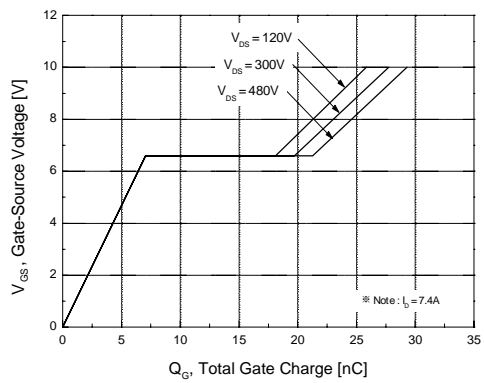


Figure 6. Gate Charge Characteristics

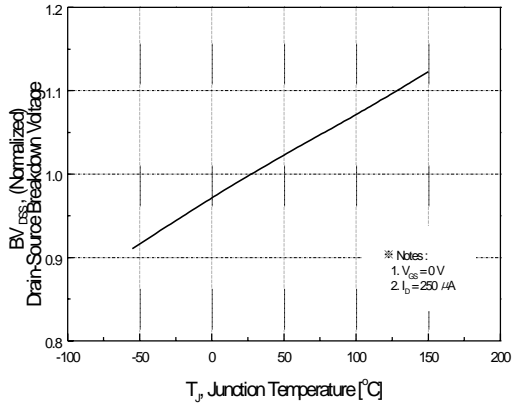


Figure 7. Breakdown Voltage Variation vs. Temperature

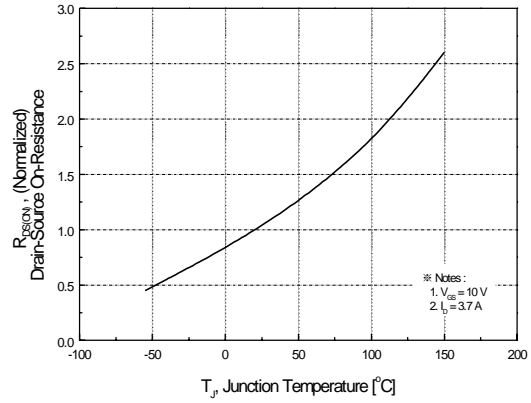


Figure 8. On-Resistance Variation vs. Temperature

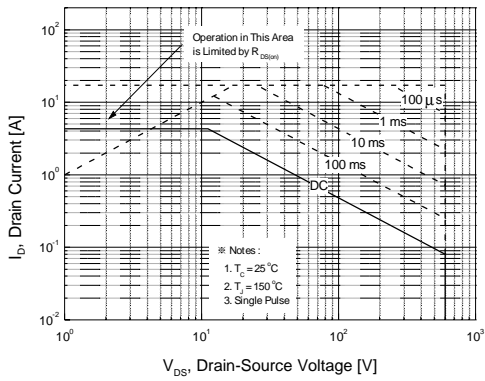


Figure 9. Maximum Safe Operating Area

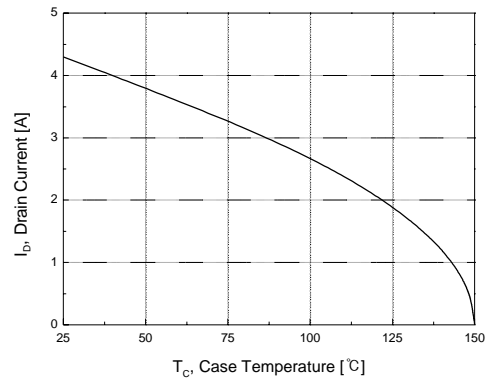


Figure 10. Maximum Drain Current vs. Case Temperature

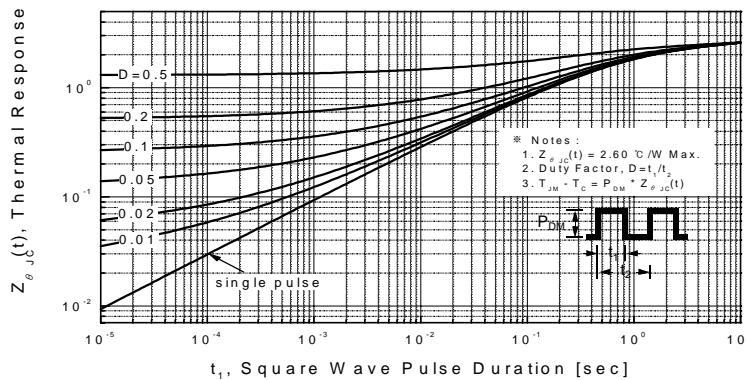
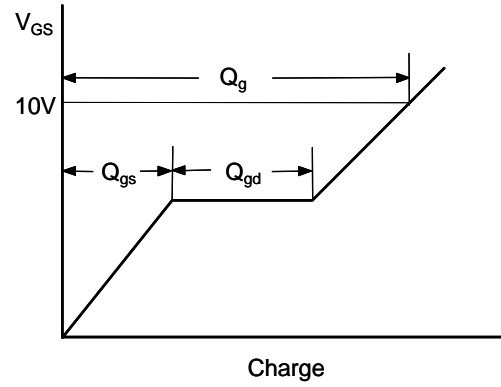
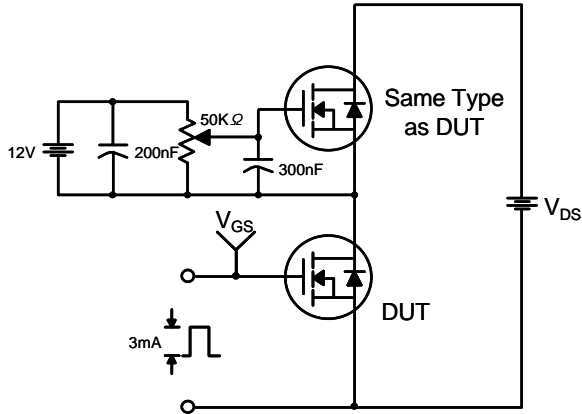
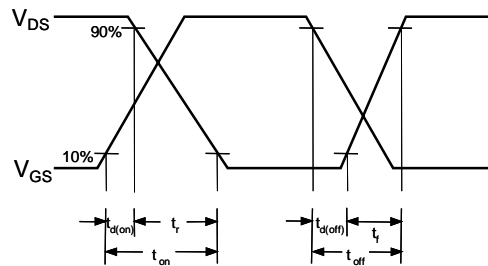
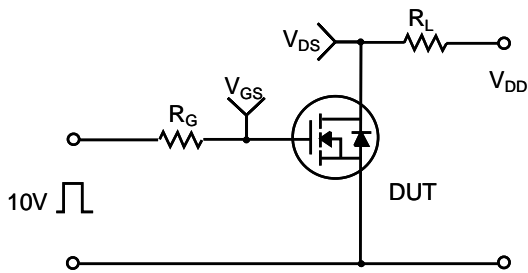


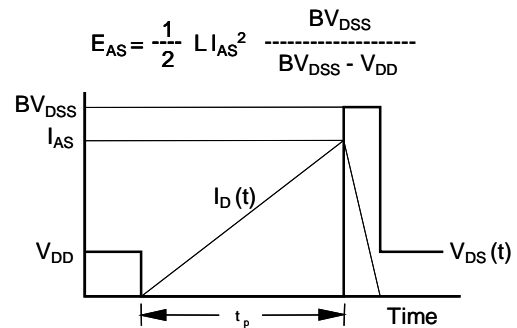
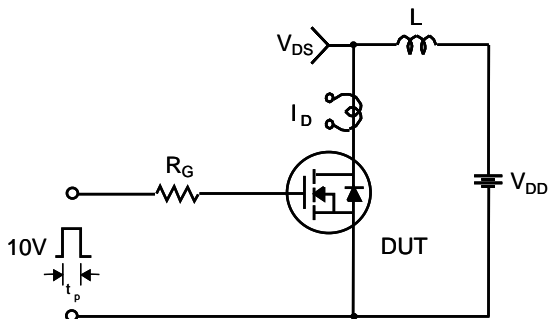
Figure 11. Transient Thermal Response Curve

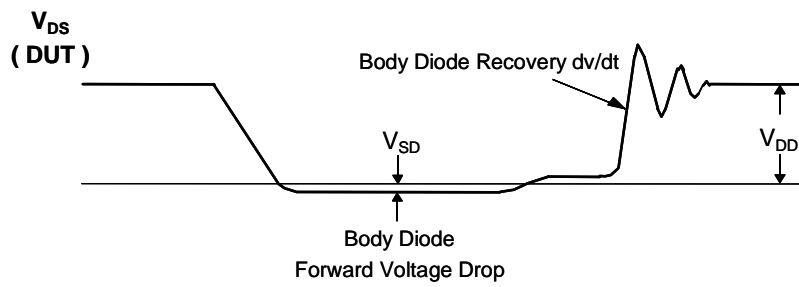
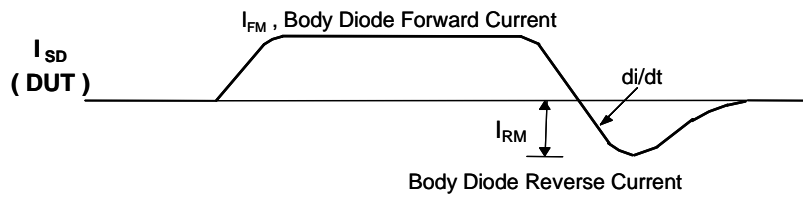
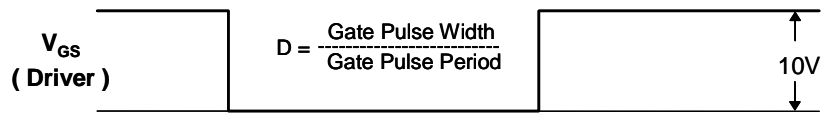
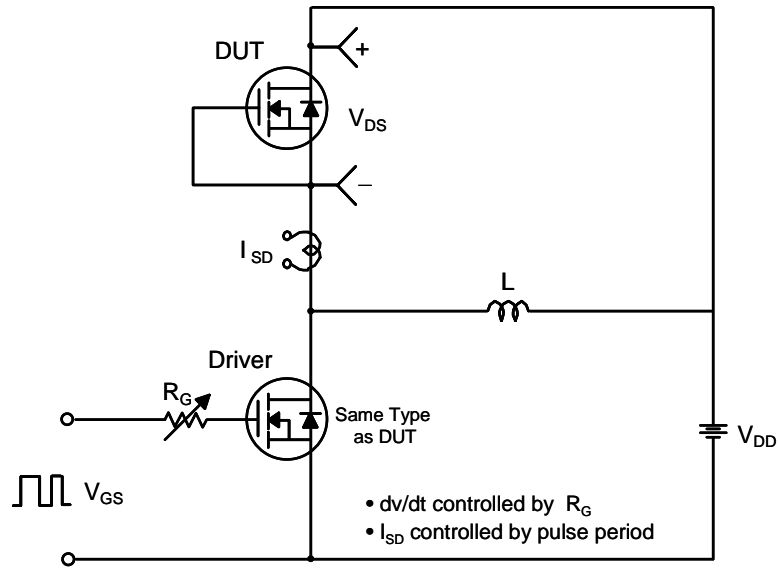


Resistive Switching Test Circuit & Waveforms



Unclamped Inductive Switching Test Circuit & Waveforms





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